

SECTION 8. H4CPlus DC ELECTRICAL CHARACTERISTICS

Table 8-1 Preliminary Electrical Considerations for H4CPlus Series Arrays

ABSOLUTE MAXIMUM RATINGS				
Symbol	Parameter	V _{DD} =3V/3.3V±0.3V	V _{DD} =5V±10%	Unit
V _{DD}	DC Supply Voltage	-0.5 to 4.6	-0.5 to 6.0	V
V _{In}	DC Input Voltage	-0.5 to V _{DD} + 0.5	-0.5 to V _{DD} + 0.5	V
V _{out}	DC Output Voltage	-0.5 to V _{DD} + 0.5	-0.5 to V _{DD} + 0.5	V
I	DC Current Drain per Pin, Any Single Input or Output	±50	±50	mA
I	DC Current Drain per Pin, Any Paralleled Outputs	±100	±100	mA
I	DC Current Drain VDD and VSS Pins	±100	±100	mA
T _{stg}	Storage Temperature	-65 to +150	-65 to +150	°C
T _L	Lead Temperature (10 second soldering)	300	300	°C

Note: Maximum ratings are those values beyond which damage to the device may occur.

RECOMMENDED OPERATING CONDITIONS (to guarantee functionality)

Symbol	Parameter	Min	Max	Unit
V _{DD} *	DC Supply Voltage, V _{DD} = 5.0V (Nominal)	4.5	5.5	V
V _{DD} *	DC Supply Voltage, V _{DD} = 3.0/3.3V (Nominal)	2.7	3.6	V

* For testing, only. V_{DD} range is wider for simulation purposes.

Notes:

1. All parameters are characterized for DC conditions after thermal equilibrium has been established.
2. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{ss} or V_{DD}).
3. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that V_{In} and V_{out} be constrained to the range V_{SS} ≤ (V_{In} or V_{out}) ≤ V_{DD}.

Table 8-2 DC Electrical Characteristics for H4CPlus Series Arrays ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Condition	$\text{TTL } V_{DD} = 3V/3.3V \pm 0.3V$ Guaranteed		$\text{TTL } V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
V_{IH}	Input High Voltage, ** CMOS Inputs (3.3V and 5V core)		2.0	$V_{DD} + 0.3$	0.7 V_{DD}	$V_{DD} + 0.3$	V
	TTL Inputs (3.3V and 5V core)		2.0	$V_{DD} + 0.3$	2.2*	$V_{DD} + 0.3$	
V_{IL}	Input Low Voltage, ** CMOS Inputs (3.3V and 5V core)		-0.3	0.8	-0.3	0.3 V_{DD}	V
	TTL Inputs (3.3V and 5V core)		-0.3	0.8	-0.3	0.8	
V_{T+}	Positive Threshold Voltage, CMOS Schmitt Trigger		-	0.75 V_{DD}	-	0.7 V_{DD}	V
	TTL Schmitt Trigger		N/A	N/A	-	2.4	
V_{T-}	Negative Threshold Voltage, CMOS Schmitt Trigger		0.25 V_{DD}	-	0.25 V_{DD}	-	V
	TTL Schmitt Trigger		N/A	N/A	0.8	-	
V_{Hy}	Hysteresis - CMOS Schmitt Trigger	V_{T+} to V_{T-}	0.1 V_{DD}		0.12 V_{DD}	-	V
	Hysteresis - TTL Schmitt Trigger		N/A	N/A	0.05 V_{DD}	-	
$I_{OH}^†$	Output High Current, ON32 Output Type	$V_{DD} = \text{Min},$ $V_{OH} \text{ Min} = 0.8V_{DD}$	-24.0	-	-48.0	-	mA
	ON16 Output Type		-12.0	-	-24.0	-	
	ON8 Output Type		-6.0	-	-12.0	-	
	ON4 Output Type		-3.0	-	-6.0	-	
	ON2 Output Type		-2.0	-	-3.0	-	
I_{OL}	Output Low Current, ON32 Output Type	$V_{DD} = \text{Min},$ $V_{OL} \text{ Max} = 0.4 \text{ Volts}$	24	-	48.0	-	mA
	ON16 Output Type		12	-	24.0	-	
	ON8 Output Type		6	-	12.0	-	
	ON4 Output Type		3	-	6.0	-	
	ON2 Output Type		2	-	3.0	-	
V_{OH}	Output High Voltage, LVC MOS	$V_{DD} = \text{Min}, I_{OH} = -100\mu\text{A}$	$OV_{DD3} - 0.2$	-	$OV_{DD3} - 0.2$	-	V
V_{OL}	Output Low Voltage, LVC MOS	$V_{DD} = \text{Min}, I_{OL} = +100\mu\text{A}$	-	0.2	-	0.2	V
I_{in}	Input Leakage Current, No Pull Resistor	$V_{in} = V_{DD}$ or V_{SS}	-5	5	-5	5	μA
	with Pullup Resistor	PUL; $V_{in} = V_{SS}$	-5	-100	-10	-200	
	with Pulldown Resistor	PDL; $V_{in} = V_{DD}$	5	100	10	200	
I_{OZ}	Output Leakage Current, 3-State Output	Output = Off-State $V_{out} = V_{DD}$ or V_{SS}	-10	10	-10	10	μA
	Output Leakage Current, Open Drain Output (Device Off)	Output = Off-State $V_{out} = V_{DD}$	-10	10	-10	10	
I_{DD}	Max Quiescent Supply Current	$I_{out} = 0\text{mA}$ $V_{in} = V_{DD}$ or V_{SS}	Design Dependent				mA

* $V_{IH} = 2.0\text{V}$ at $V_{DD} = 5V \pm 5\%$

** Use 3.3V system interface voltage for macros: ICXN, ICXNH, BICXN, ISXN, ISXNH, and BISXN.

† For $3.3V \pm 0.3$ and $5V \pm 10\%$, only. For 2.7 V consult factory.†† V_{DD} refers to the System interface Voltage

N/A = Not Applicable

Table 8-3 DC Electrical Characteristics for H4CPlus Series GTL Driver ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Conditions	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
DC Characteristics for GTL Receivers							
V_{IH}	Input High Voltage, GTL Inputs	-	$V_{VR08} + 0.10$	$V_{DD} + 0.30$	$V_{VR08} + 0.10$	$V_{DD} + 0.30$	V
V_{IL}	Input Low Voltage, GTL Inputs	-	-0.30	$V_{VR08} - 0.10$	-0.30	$V_{VR08} - 0.10$	V
V_{IDH}	Minimum Input High Voltage, GTL Differential Input	-	-	100	-	100	mV
V_{IDL}	Input Low Voltage, GTL Differential Input	-	-	100	-	100	mV
V_{ICM}	Input Common Mode Voltage Range, V_{CM} min	-	0.40	-	0.6	-	V
	V_{CM} max		-	1.1	-	2.0	V
I_{IH}	Input High Current, GTL Input	$V_{in} = V_{TT}, V_{DD} = \text{Max}$	-	5	-	5	μA
I_{IL}	Input Low Current, GTL Inputs	$V_{in} = 0.4V, V_{DD} = \text{Max}$	-	-5	-	-5	μA
V_{VR08}	GTL Ref. Voltage	-	0.68	0.90	0.68	0.90	V
I_{DD}^*	Typical Quiescent Supply Current	-	-	1.3	-	3.8	mA
DC Characteristics for GTL Drivers							
V_{OH}	Output High Voltage, 20mA Output Macros	$I_{OH} = -10\mu\text{A}, V_{DD} = \text{Min}$	$V_{TT} - 0.05$	$V_{TT} + 0.05$	$V_{TT} - 0.05$	$V_{TT} + 0.05$	V
	40mA Output Macros	$I_{OH} = -10\mu\text{A}, V_{DD} = \text{Min}$	$V_{TT} - 0.05$	$V_{TT} + 0.05$	$V_{TT} - 0.05$	$V_{TT} + 0.05$	
V_{OL}	Output Low Voltage, 20mA Output Macros	$I_{OL} = 20\text{mA}, V_{DD} = 3\text{ V}$	-	0.4	-	-	V
	40mA Output Macros	$I_{OL} = 40\text{mA}, V_{DD} = 3\text{ V}$	-	0.4	-	-	
V_{OL}	Output Low Voltage, 20mA Output Macros	$I_{OL} = 24\text{mA}, V_{DD} = 4.5\text{ V}$	-	-	-	0.4	V
	40mA Output Macros	$I_{OL} = 48\text{mA}, V_{DD} = 4.5\text{ V}$	-	-	-	0.4	
V_{OD}	Differential Output Voltage, 20mA Output Macros	$I_{OL} = 20\text{mA}$	$V_{TT} - 0.45$	-	-	-	V
		$I_{OL} = 24\text{mA}$	-	-	$V_{TT} - 0.45$	-	
I_{OZH}	GTL Output Off Current High	$V_{out} = 1.2V, V_{DD} = \text{Max}$	-	10	-	10	μA
I_{OZL}	GTL Output Off Current Low	$V_{out} = 0.4V, V_{DD} = \text{Max}$	-	-10	-	-10	μA

* Not tested.

Notes:

1. Recommended: $V_{TT} = 1.2V \pm 5\%$, $V_{VR08} = (2/3) V_{TT}$, $R_T = 25\Omega/50\Omega$, $V_{TT} \text{ MAX} = V_{DD} + 0.3V$

Table 8-4 DC Electrical Characteristics for H4CPlus CMTL Buffers ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Conditions	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
DC Characteristics for CMTL Receivers							
V_{IDH}	Minimum Input High Voltage, CMTL Inputs (Differential)	-	-	100	-	100	mV
V_{IDL}	Maximum Input Low Voltage, CMTL Inputs (Differential)	-	-	100	-	100	mV
V_{ICM}	Input Common Mode Voltage Range, V_{ICM} Min	V_{DD} max	0.6	-	1.0	-	V
	V_{ICM} Max	V_{DD} min	-	2.2	-	3.5	V
I_{IH}	Input High Current, CMTL Inputs (No Termination)	$V_{in} = V_{OH}$ max, $V_{DD} = $ Max	-	5	-	5	μA
I_{IL}	Input Low Current, CMTL Inputs (No Termination)	$V_{in} = V_{OL}$ min, $V_{DD} = $ Max	-	5	-	5	μA
I_{DD}^*	Max Quiescent Supply Current	-	-	1.8	-	4.7	mA
DC Characteristics for CMTL Drivers							
V_{OH}	Minimum Output High Voltage, CMTL Outputs (no Load)**	$V_{DD} = $ Min	-	-	2.5	3.7	V
	CMTL Outputs (50 Ω)†		1.3	2.0	2.4	3.1	
	CMTL Outputs (100 Ω)†		1.4	2.1	2.5	3.2	
	CMTL Outputs $I_{OH} = 0.5\text{mA}$		N/A	N/A	-	3.5	
V_{OL}	Maximum Output Low Voltage, CMTL Outputs (no Load)**	$V_{DD} = $ Min	-	-	1.0	2.0	V
	CMTL Outputs (50 Ω)†		1.1	2.0	1.6	2.4	
	CMTL Outputs (100 Ω)†		1.0	1.9	1.5	2.3	
	CMTL Outputs $I_{OL} = 20\text{mA}$		N/A	N/A	1.7	2.7	
IV_{ODI}	Differential Output Voltage, CMTL Outputs (no Load)**	$V_{DD} = $ Min	-	-	1.0	2.5	V
	CMTL Outputs (50 Ω)†		0.19 Typ.		0.4	1.1	
	CMTL Outputs (100 Ω)†		0.29 Typ.		0.5	1.4	
V_{OS}	Output Offset Voltage, CMTL Outputs (no Load)**	$V_{DD} = $ Min	-	-	2.1	2.6	V
	CMTL Outputs (50 Ω)†		1.35	1.85	2.1	2.65	
	CMTL Outputs (100 Ω)†		1.35	1.85	2.1	2.65	
I_{OZH}	CMTL Output Off Current High	$V_{out} = V_{DD}$, $V_{DD} = $ Max	-10	10	-10	10	μA
I_{OZL}	CMTL Output Off Current Low	$V_{out} = V_{SS}$, $V_{DD} = $ Max	-10	10	-10	10	μA
R_o	Output Impedance (Typical)	$100\Omega \leq \text{Load} \leq 200\Omega$ †	50		30		Ω

* Not tested.

** OD32TCMT and BOD32TCMT macros, only.

† Loads across differential CMTL outputs.

N/A = Not Applicable

Table 8-5 Electrical Characteristics for H4CPlus PECL Receivers ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Conditions	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
DC Characteristics for PECL Receivers							
V_{IH}	Input High Voltage, PECL Single-Ended	-	$V_{VR38} + 0.10$	$V_{DD} + 0.30$	$V_{VR38} + 0.10$	$V_{DD} + 0.30$	V
V_{IL}	Input Low Voltage, PECL Single-Ended	-	-0.30	$V_{VR38} - 0.10$	-0.30	$V_{VR38} - 0.10$	V
V_{IDH}	Minimum Input High Voltage, PECL Differential Input	-	-	100	-	100	mV
V_{IDL}	Input Low Voltage, PECL Differential Input	-	-	100	-	100	mV
V_{ICM}	Input Common Mode Voltage Range, V_{CM} min	-	1.2	-	1.4	-	V
	V_{CM} max		-	$V_{DD} - 0.8$	-	$V_{DD} - 0.8$	V
I_{IH}	Input High Current, PECL Input	$V_{in} = V_{DD}$, $V_{DD} = \text{Max}$	-	5	-	5	μA
I_{IL}	Input Low Current, PECL Input	$V_{in} = V_{SS}$, $V_{DD} = \text{Max}$	-	5	-	5	μA
I_{DD^*}	Max Quiescent Supply Current	-	-	1.5 (ILP-) 5.3 (IPX-)	-	4.3 (IPD) 5.1 (IPN)	mA
V_{VR38}	PECL Reference Voltage	PECL Single-Ended	$V_{DD} - 1.3$ Typ.		$V_{DD} - 1.3$ Typ.		V

* Not tested.

Table 8-6 DC Electrical Characteristics for H4CPlus Series PCI Buffers ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Condition	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
DC Characteristics for PCI Receivers							
V_{IH}	Input High Voltage		$0.5V_{DD}$	$V_{DD} + 0.5$	2.0	$V_{DD} + 0.5$	V
V_{IL}	Input Low Voltage		-0.5	$0.3V_{DD}$	-0.5	0.8	V
I_{IH}	Input High Leakage Current	3.3 V: $0 < V_{in} < V_{DD}$ 5.0 V: $V_{in} = 2.7$ V	-	10	-	70	μA
I_{IL}	Input Low Leakage Current	3.3 V: $0 < V_{in} < V_{DD}$ 5.0 V: $V_{in} = 0.5$ V	-	-10	-	-70	μA
DC Characteristics for PCI Drivers							
V_{OH}	Output High Voltage	3.3 V: $I_{out} = -500 \mu\text{A}$ 5.0 V: $I_{out} = -2 \text{ mA}$	$0.9V_{DD}$	-	2.4	-	V
V_{OL}	Output Low Voltage	3.3 V: $I_{out} = 1500 \mu\text{A}$ 5.0 V: $I_{out} = 6 \text{ mA}$	-	$0.1V_{DD}$	-	0.55	V
AC Characteristics for PCI Drivers (Not Tested)							
V_{OHmin}	Output High Voltage Minimum	3.3 V: $I_{out} = -12(V_{DD})\text{mA}$ 5.0 V: $I_{out} = -44 \text{ mA}$	$0.3V_{DD}$	-	1.4	-	V
V_{OHmax}	Output High Voltage Maximum	3.3 V: $I_{out} = -32(V_{DD})\text{mA}$ 5.0 V: $I_{out} = -142 \text{ mA}$	-	$0.7V_{DD}$	-	3.1	V

Table 8-6 DC Electrical Characteristics for H4CPlus Series PCI Buffers ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Condition	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
V_{OLmin}	Output Low Voltage Minimum	$3.3V: I_{out} = 38(V_{DD}) \text{ mA}$ $5.0V: I_{out} = 206 \text{ mA}$	0.18 V_{DD}	-	0.71	-	V_{OL} min
V_{OLmax}	Output Low Voltage Maximum	$3.3V: I_{out} = 16(V_{DD}) \text{ mA}$ $5.0V: I_{out} = 95 \text{ mA}$	-	0.6 V_{DD}	-	2.2	V_{OL} max

Table 8-7 DC Electrical Characteristics for H4CPlus Series Fail-Safe and Extended Voltage Range Bidirectional I/O ($T_a = -40^\circ\text{C}$ to 85°C)

Sym.	Parameter	Condition	$V_{DD} = 3.3V \pm 0.3V$ Guaranteed		$V_{DD} = 5V \pm 10\%$ Guaranteed		Unit
			Min.	Max.	Min.	Max.	
Leakage Current for Fail-Safe and Extended Voltage Range Bidirectional I/O							
I_{off}	Leakage Current for bidirectional Fail-Safe I/O, i.e: ON8TF and BON8TF No pull resistor	$V_{DD} = OV_{DD5} = 0$ to MAX $V_{in} = V_{DD}$ or V_{SS} Output = Off-State	-	-	-20	+20	μA
	Leakage Current for bidirectional Fail-Safe I/O, with pulldown resistor	$V_{DD} = OV_{DD5} = 0$ to MAX $V_{in} = V_{DD}$ or V_{SS} Output = Off-State	-	-	-20	+200	
I_{off}	Leakage Current for Fail-Safe Outputs with Regulator, i.e: ON8TFA and BON8TFA No pull resistor	$V_{DD} = OV_{DD5} = \leq 2.5V$ $V_{in} = 0$ to 5.5 V Output = Enabled	-	-	-20	+20	μA
	Leakage Current for Fail-Safe Outputs with Regulator, i.e: ON8TFA and BON8TFA with pulldown resistor	$V_{DD} = OV_{DD5} = \leq 2.5V$ $V_{in} = 0$ to 5.5 V Output = Enabled	-	-	-20	+200	
I_{off}^*	Leakage Current for bidirectional extended voltage range I/O, No pull resistor	$V_{in} = 0$ to 5.5 V Output = Off-State	-20	+20	-	-	μA
	Leakage Current for bidirectional extended voltage range I/O, with pulldown resistor	$V_{in} = 0$ to 5.5 V Output = Off-State	-20	+200	-	-	

*For the bidirectional extended voltage range I/O, the bidirectional input macro must be a 3.3V System and 3.3V Core macro.

N/A = Not Applicable